

10 TO 4 LINE PRIORITY ENCODER

- HIGH SPEED
 - $t_{PD} = 15 \text{ ns} (TYP.) \text{ at } V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 4 \mu A \text{ (MAX.)}$ at $I_{A} = 25 \text{ °C}$
- HIGH NOISE IMMUNITY

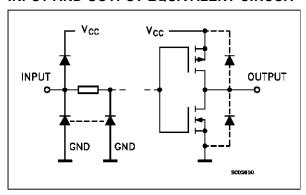
 VNIH = VNIL = 28 % VCC (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE | I_{OH} | = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V to 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS147

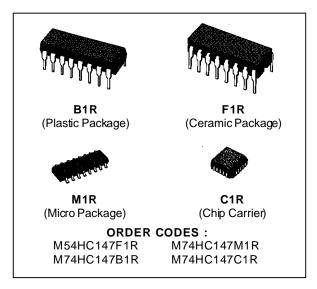
DESCRIPTION

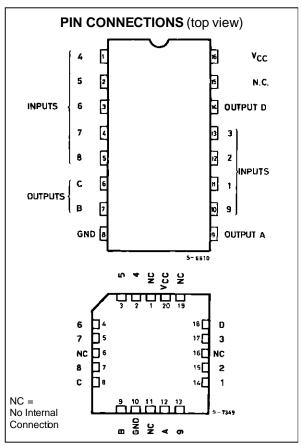
The M54/74HC147 is a high speed CMOS 10 TO 4 LINE PRIORITY ENCODER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

This device features priority encoding of the inputs to ensure that only the highest order data line is encoded. Nine input lines are encoded to a four line BCD output. The implied decimal zero condition requires no input condition as zero is encoded when all nine data lines are at high logic level. All data input and outputs are active at the low logic level. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT







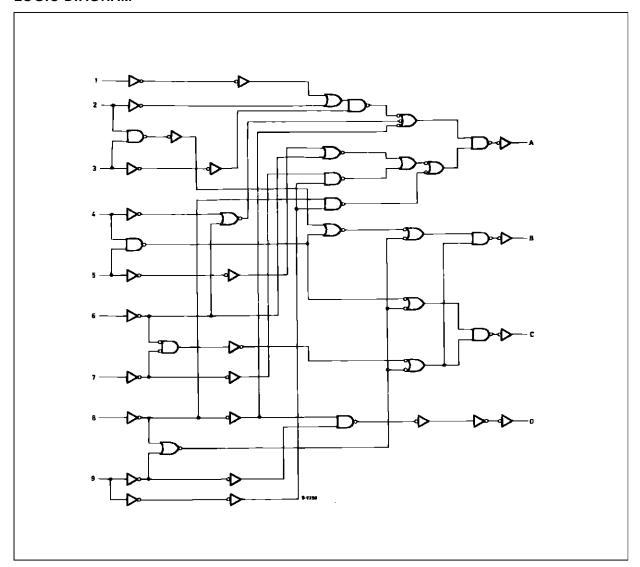
October 1992 1/10

TRUTH TABLE

				INPUTS						OUTI	PUTS	
1	2	3	4	5	6	7	8	9	D	C	В	Α
Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
Χ	X	Х	Х	Х	Х	Х	Х	L	L	Η	Н	L
Х	Х	Х	Х	Х	Х	Х	L	Н	L	Н	Н	Н
Χ	Х	X	Х	Х	Х	L	Н	Н	Η	L	L	L
Х	X	Х	Х	Х	L	Н	Н	Н	Η	L	L	Н
Χ	Χ	Х	Χ	L	Н	Н	Н	Н	Н	L	Н	L
Х	X	Х	L	Н	Н	Н	Н	Н	Н	L	Н	Н
Х	Х	L	Н	Н	Н	Н	Н	Н	Н	Н	L	L
X	L	Η	Η	Н	Н	Н	Н	Н	Η	Η	L	Н
L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L

X: Don't Care

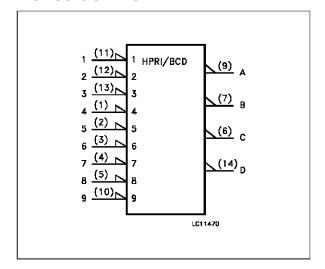
LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
9, 7, 6, 14	A to D	BCD Address Outputs (Active LOW)
11, 12, 13, 1, 2, 3, 4, 5, 10	1 to 9	Decimal Data Inputs (Active LOW)
15	NC	Not Connected
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
lıĸ	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V _{CC}	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	ဂိ ဂိ
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000	ns
		V _{CC} = 4.5 V	0 to 500	
		$V_{CC} = 6 V$	0 to 400	

DC SPECIFICATIONS

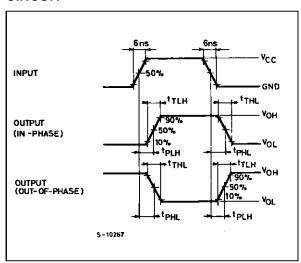
		Te	est Co	nditions	Value							
Symbol	Parameter	Vcc			$T_A = 25$ °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	1.8
V_{OH}	High Level	2.0	Vı =		1.9	2.0		1.9		1.9		
	Output Voltage	4.5	VI =	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	V _{IL}	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		lo=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	Vı =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VI =	I _O = 20 μA		0.0	0.1		0.1		0.1	
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	VIL	I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
lı	Input Leakage Current	6.0	V _I = '	V _{CC} or GND			±0.1		±1		±1	μΑ
Icc	Quiescent Supply Current	6.0	V _I = '	V _{CC} or GND			4		40		80	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

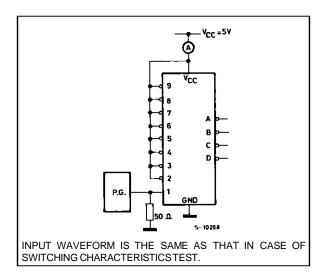
		Test Condition	ıs			Value				
Symbol	Parameter	Vcc (V)		A = 25 C		1	85 °C HC	1	125 °C HC	Unit
		(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH}	Output Transition	2.0		30	75		95		110	
t _{THL}	Time	4.5		8	15		19		22	ns
		6.0		7	13		16		19	
t _{PLH}	Propagation	2.0		60	125		190		225	
t _{PHL}	Delay Time	4.5		18	30		38		45	ns
		6.0		15	26		32		38	
C _{IN}	Input Capacitance			5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance			24						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. I_{CC}(opr) = C_{PD} • V_{CC} • f_{IN} + I_{CC}

SWITCHING CHARACTERISTICS TEST CIRCUIT

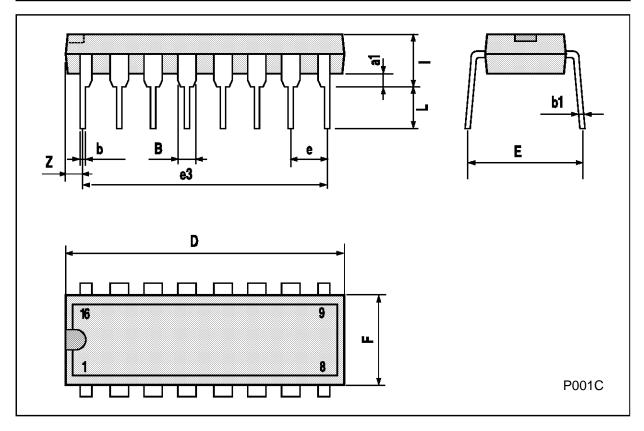


TEST CIRCUIT Icc (Opr.)



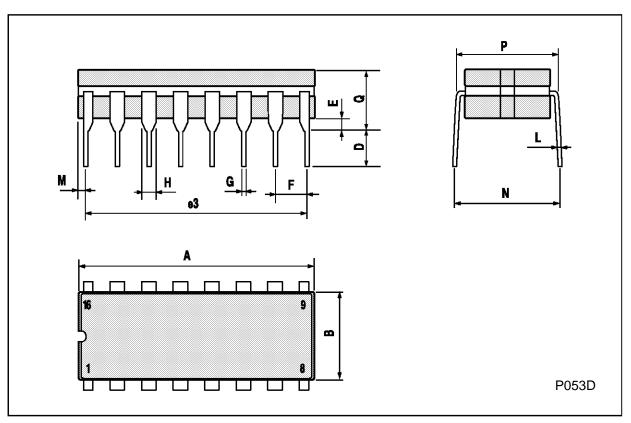
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



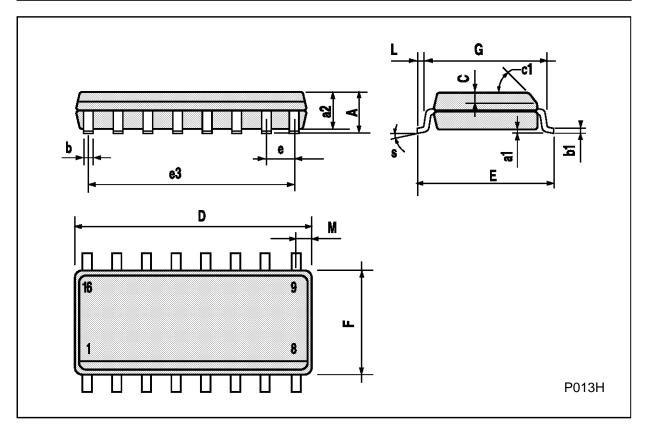
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm		inch				
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			20			0.787		
В			7			0.276		
D		3.3			0.130			
Е	0.38			0.015				
e3		17.78			0.700			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
Н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
M	0.51		1.27	0.020		0.050		
N			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		



SO16 (Narrow) MECHANICAL DATA

DIM.		mm		inch				
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.004		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	9.8		10	0.385		0.393		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S			8° (ı	max.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch				
Diiii.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А	9.78		10.03	0.385		0.395		
В	8.89		9.04	0.350		0.356		
D	4.2		4.57	0.165		0.180		
d1		2.54			0.100			
d2		0.56			0.022			
E	7.37		8.38	0.290		0.330		
е		1.27			0.050			
e3		5.08			0.200			
F		0.38			0.015			
G			0.101			0.004		
М		1.27			0.050			
M1		1.14			0.045			



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